

200mA 40V Low VF(0.37mm)

Chip Information

Chip Size	0.37 x 0.37mm
Pad Size	0.30 x 0.30mm
Chip Quantity	80698 pcs/wafer
Scribe Line Width	40um
Passivation	PSG
Wafer Size	5inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	30	V	
Average Forward Rectified Current	IF(AV)	200	mA	
Peak Forward Surge Current	IFSM	1	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.500	0.465	0.410	V	IF=200mA Ta=25degC
	VF2	0.350	0.325	0.230	V	IF=10mA Ta=25degC
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	30	15	6	uA	VR=10V Ta=25degC
	IR2	100	40	11	uA	VR=20V Ta=25degC
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	40	44	52	V	IR=500uA
Junction Capacitance	Cj				pF	
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back Metal
YHA06B	140 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)
YHA06C	140 +/- 20um	Au(For Eutectic)
YHA06Y	120 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:
Designed For RB521S-30